

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1-37. (Canceled)

38. (Currently Amended) The patterning method according to ~~claim 37,~~claim 70, the first liquid material being the same as the second liquid material.

39. (Currently Amended) The patterning method according to ~~claim 37,~~claim 70, the first liquid material being different from the second liquid material.

40-44. (Canceled)

45. (Currently Amended) The patterning method according to ~~claim 44~~claim 74 wherein the ~~indent region is~~plurality of indents are provided with a castellated cross-sectional profile.

46. (Currently Amended) The patterning method according to ~~claim 44~~claim 74 wherein the ~~indent region is~~plurality of indents are provided with a saw-tooth cross-sectional profile.

47. (Currently Amended) The patterning method according to ~~claim 44~~claim 74 comprising providing first and second indent regions of elongate shape and impressing a further elongate indent region arranged between but spaced from the first and second indent regions, the further indent region having a substantially planar bottom surface.

48. (Currently Amended) A method of manufacturing an electronic device, the method comprising: making a pattern by the patterning method according to ~~claim 37,~~claim 70.

49. (Previously Presented) The method according to claim 48,
the first liquid material including a semiconductor material, and the second liquid material including a semiconductor material.

50. (Currently Amended) The method according to claim 49,

a source of a transistor and a drain of the transistor being formed in ~~the first~~
first part between a first indent of the plurality of indents, and the second
between the first indent and a third indent of the plurality of indents, respectively; and
a channel of the transistor being formed between the first part and the second
part.

51. (Currently Amended) A patterning method comprising:

forming an indent region in the surface of a substrate;
depositing a liquid material onto the surface at selected locations such that
spread of the material over the surface is controlled by the indent region;
wherein the indent region is formed with a cross-sectional profile to provide a
secondary barrier to further control the spread of the material over the surface; and
wherein the material is selected to comprise a semiconductor material and the
selected locations comprise the surface between ~~the elongate~~elongate indent regions so as to
provide source and drain regions for a thin film transistor having a channel length
determined by the width of ~~the further~~further elongate indent regions and a channel width
determined by the length of the further elongate indent region.

52-58. (Canceled)

59. (Currently Amended) ~~A patterning method according to claim 58,~~A patterning

method for depositing a liquid onto a surface of a substrate; said method comprising:

forming a first and second indent in the surface, each indent having falling
edges co-incident with the surface and spaced a distance apart, and in which said-forming said
~~first~~the first and second indents includes forming wall portions sloping relative to the
~~surface~~surface;

depositing said liquid between said indents; and

selecting the distance such that a greater volume of liquid is deposited and retained than in the absence of at least one of the indents.

60. (Currently Amended) A method of manufacturing an electronic device, the method comprising: making a pattern by the patterning method according to ~~claim 58~~claim 59.

61. (Canceled)

62. (Currently Amended) ~~A patterning method according to claim 61,~~ A patterning method for depositing a liquid onto a surface of a substrate, said method comprising:
forming a first and second indent in the surface, each indent having falling edges co-incident with the surface and spaced a distance apart, and in which said-forming said firstthe first and second indents includes forming wall portions sloping relative to the surface:surface;
depositing said liquid between said indents; and
selecting the distance such that a greater contact angle between the liquid and the surface is provided than in the absence of at least one of the indents.

63. (Currently Amended) A method of manufacturing an electronic device, the method comprising: making a pattern by the patterning method according to ~~claim 61~~claim 62.

64. (Canceled)

65. (Currently Amended) ~~A patterning method according to claim 64,~~ A patterning method for depositing a liquid onto a surface of a substrate, said method comprising:
forming a first and second indent in the surface, each indent having falling edges co-incident with the surface and spaced a distance apart, and in which said-forming said firstthe first and second indents includes forming wall portions sloping relative to the surface:surface;

depositing said liquid between said indents; and
selecting the distance such that the diameter of the deposited liquid is greater
than the distance.

66. (Currently Amended) A method of manufacturing an electronic device, the method comprising: making a pattern by the patterning method according to ~~claim~~
~~64~~claim 65.

67. (Canceled)

68. (Currently Amended) ~~A patterning method according to claim 67,~~A patterning
method for depositing a liquid onto a surface of a substrate, said method comprising:
forming a first and second indent in the surface, each indent having falling
edges co-incident with the surface and spaced a distance apart, and in which ~~said-forming said~~
~~first~~the first and second indents includes forming wall portions sloping relative to the
~~surface~~surface;

depositing said liquid between said indents; and
selecting the distance such that the thickness of the liquid deposited and
retained is greater than in the absence of at least one of the indents.

69. (Currently Amended) A method of manufacturing an electronic device, the method comprising: making a pattern by the patterning method according to ~~claim~~
~~67~~claim 68.

70. (New) A patterning method, comprising:
depositing a first liquid material on a substrate; and
depositing a second liquid material on a substrate
a plurality of indents being formed in the substrate, and

the plurality of indents being formed between the first liquid material deposited by the depositing of the first liquid material and the second liquid material deposited by the depositing of the second liquid material.

71. (New) A patterning method, comprising:
depositing a first liquid material on a substrate; and
depositing a second liquid material on a substrate,
an indent being formed in a surface of the substrate, and
the indent being formed between the first liquid material deposited by the depositing of the first liquid material and the second liquid material deposited by the depositing of the second liquid material, and
the indent has a width tapering towards the bottom.

72. (New) A patterning method, comprising:
depositing a first liquid material on a substrate; and
depositing a second liquid material on a substrate,
an indent being formed in a surface of the substrate, and
the indent being formed between the first liquid material deposited by the depositing of the first liquid material and the second liquid material deposited by the depositing of the second liquid material, and
the indent has a width widening towards the bottom.

73. (New) A patterning method according to claim 70, each of the plurality of indents having wall portions which have slopes relative to a surface of a surface of the substrate.

74. (New) The patterning method according to claim 73, the plurality of indents being formed with a cross-sectional profile to a secondary barrier to control spread of the first liquid material and the second liquid material.

75. The patterning method according to claim 70, further comprising:
adjusting wetting characteristic of a surface of the substrate relative to the first liquid material and the second liquid material.
76. The patterning method according to claim 70, each of the plurality of indents having a substantially planar bottom surface.
77. The patterning method according to claim 70, further comprising the plurality of indents by an impression technique.
78. The patterning method according to claim 77, the impression technique using at least one of a stamping die and a moulding technique.
79. The patterning method according to claim 70, the first liquid material including a conductive material.